



DMT69M5LFVW

PowerDI3333-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max Tc = +25°C
60V	8.3mΩ @ V _{GS} = 10V	40.6A
000	12.5mΩ @ V _{GS} = 4.5V	33.1A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications

- Backlighting
- Power Management Functions
- **DC-DC Converters**

Features

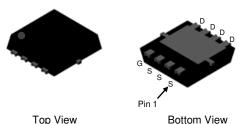
100% Unclamped Inductive Switching (UIS) Test in Production-Ensures More Reliable and Robust End Application

60V N-CHANNEL ENHANCEMENT MODE MOSFET

- Low On-Resistance
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)





Part Number	Case	Packaging
DMT69M5LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2000/Tape & Reel
DMT69M5LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3000/Tape & Reel

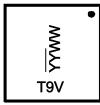
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

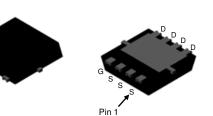
Marking Information



T9V = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

PowerDI3333-8 (SWP) (Type UX)

Equivalent Circuit





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
	Tc = +25°C	1-	40.6	А
	Tc = +70°C	lD	32.5	
Continuous Drain Current (Note 5) V _{GS} = 10V	TA = +25°C	ام	14.8	А
	T _A = +70°C		11.9	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	•	Ідм	160	А
Maximum Continuous Body Diode Forward Current (Note 5)	ls	40	А	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%	I _{SM}	160	А	
Avalanche Current, L = 0.1mH	las	27.4	А	
Avalanche Energy, L = 0.1mH	Eas	37.5	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.74	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	45.6	°C/W
Total Power Dissipation (Note 6) $T_{C} = +25^{\circ}C$		PD	20.5	W
Thermal Resistance, Junction to Case (Note 6)		R _{0JC}	6.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-			T 10 IVI	
	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			1	1			
Drain-Source Breakdown Voltage	BVDSS	60	—	—	V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	IDSS	—	—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	1.4	—	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		—	6.2	8.3	mΩ	V _{GS} = 10V, I _D = 13.5A	
Static Drain-Source On-Resistance	RDS(ON)		9.2	12.5	11122	V _{GS} = 4.5V, I _D = 11.5A	
Diode Forward Voltage	Vsd	_	0.8	1.2	V	V _{GS} = 0V, I _S = 13.5A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	—	1406	_	pF		
Output Capacitance	Coss	—	540		рF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	—	52	—	pF		
Gate Resistance	Rg	_	1.85	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	—	28.4	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	15.4	_	nC		
Gate-Source Charge	Qgs	_	2.4	_	nC	V _{DS} = 30V, I _D = 13.5A	
Gate-Drain Charge	Qgd	—	9.0	_	nC	1	
Turn-On Delay Time	td(on)	_	10.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_g = 6\Omega, I_D = 13.5A$	
Turn-On Rise Time	tR	_	49.0	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	30.9	_	ns		
Turn-Off Fall Time	tF	—	79.5	—	ns		
Body Diode Reverse Recovery Time	t _{RR}	—	26.7	—	ns		
Body Diode Reverse Recovery Charge	Qrr		44.8	_	nC	I⊧ = 13.5A, di/dt = 300A/µs	

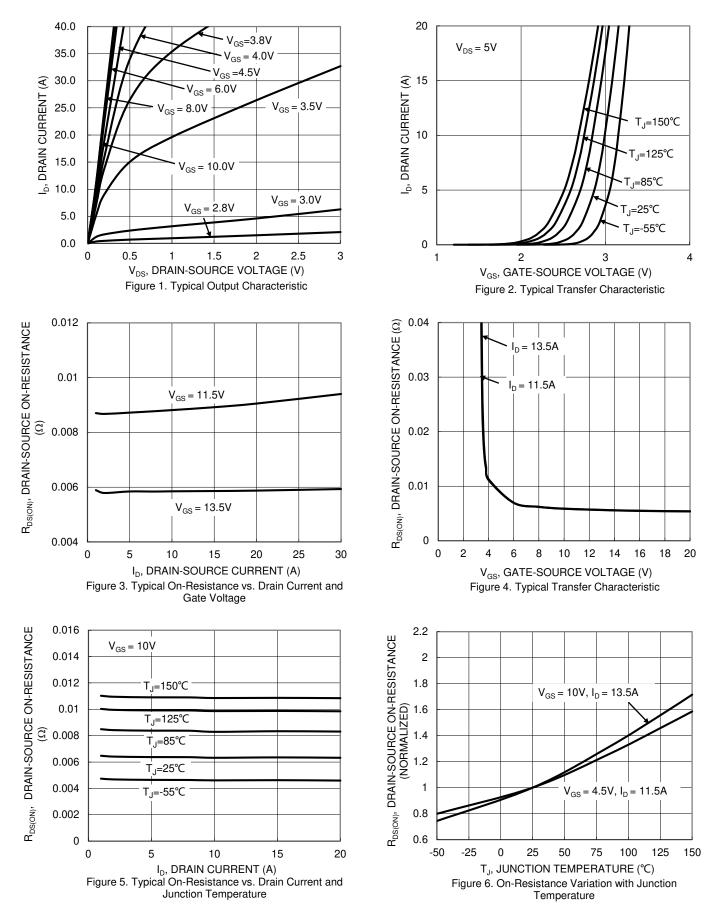
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

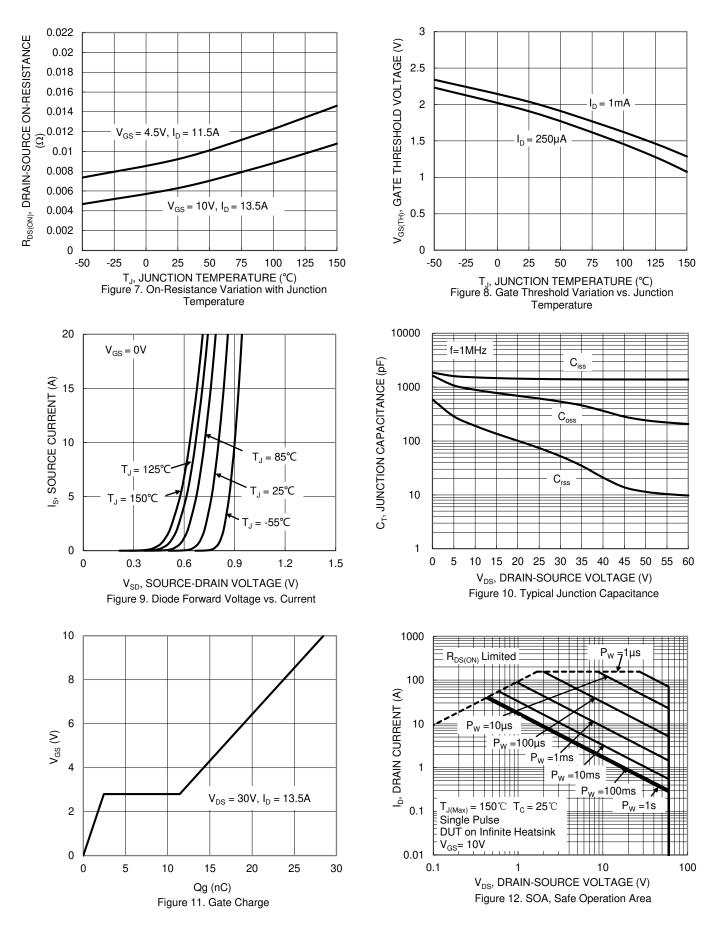
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



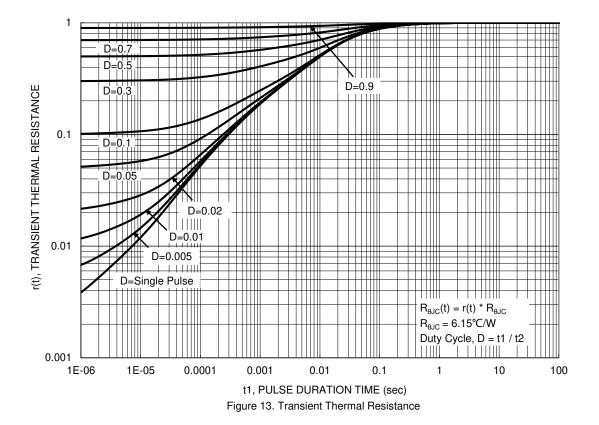
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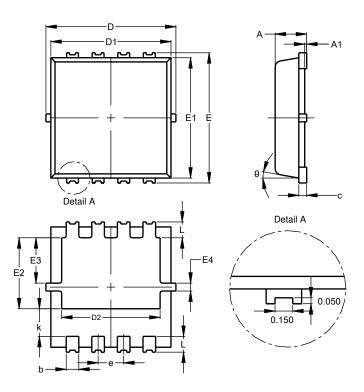






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



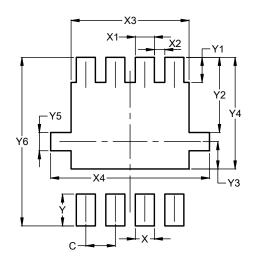
PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.600		
X4	3.500		
Y	0.700		
Y1	0.550		
Y2	1.650		
Y3	0.600		
Y4	2.450		
Y5	0.400		
Y6	3.700		



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